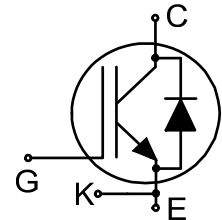


TRENCHSTOP™ 5 soft switching IGBT

TRENCHSTOP™ 5 high speed soft switching IGBT copacked with full current rated RAPID 1 fast and soft antiparallel diode

Features and Benefits:

- High speed S5 technology offering
- High speed smooth switching device for hard & soft switching
 - Very Low V_{CEsat} , 1.42V at nominal current
 - Plug and play replacement of previous generation IGBTs
 - 650V breakdown voltage
 - Low gate charge Q_G
 - IGBT copacked with full rated RAPID 1 fast antiparallel diode
 - Maximum junction temperature 175°C
 - Qualified according to JEDEC for target applications
 - Pb-free lead plating; RoHS compliant
 - Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>



Applications:

- Industrial UPS
- Industrial SMPS
- Energy Storage
- Charger
- Welding

Product Validation:

Qualified for applications listed above based on the test conditions in the relevant tests of JEDEC20/22

Package pin definition:

- Pin C & backside - collector
- Pin E - emitter
- Pin K - Kelvin emitter
- Pin G - gate

Please note: The emitter and Kelvin emitter pins are not exchangeable. Their exchange might lead to malfunction.



Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat} , $T_{vj}=25^\circ\text{C}$	T_{vjmax}	Marking	Package
IKZ50N65ES5	650V	50A	1.35V	175°C	K50EES5	PG-TO247-4

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TRENCHSTOP™ 5 soft switching IGBT

Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	650	V
DC collector current, limited by $T_{vjmax}^{1)}$ $T_C = 25^{\circ}\text{C}$ value limited by bondwire $T_C = 100^{\circ}\text{C}$	I_C	80.0 60.5	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	200.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$	-	200.0	A
Diode forward current, limited by $T_{vjmax}^{1)}$ $T_C = 25^{\circ}\text{C}$ value limited by bondwire $T_C = 100^{\circ}\text{C}$	I_F	80.0 60.5	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	200.0	A
Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$)	V_{GE}	± 20 ± 30	V
Power dissipation $T_C = 25^{\circ}\text{C}$ Power dissipation $T_C = 100^{\circ}\text{C}$	P_{tot}	274.0 137.0	W
Operating junction temperature	T_{vj}	-40...+175	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55...+150	$^{\circ}\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R _{th} Characteristics						
IGBT thermal resistance, junction - case	R _{th(j-C)}		-	-	0.55	K/W
Diode thermal resistance, junction - case	R _{th(j-C)}		-	-	0.63	K/W
Thermal resistance junction - ambient	R _{th(j-a)}		-	-	40	K/W

¹⁾ value limited by bondwire

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Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 0.20mA$	650	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0V, I_C = 50.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 175^{\circ}C$	- - -	1.35 1.50 1.60	1.70 - -	V
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 50.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 175^{\circ}C$	- - -	1.45 1.42 1.39	1.70 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.50mA, V_{CE} = V_{GE}$	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 650V, V_{GE} = 0V$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	- 2000	50 -	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 50.0A$	-	62.0	-	S

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C _{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	-	3100	-	pF
Output capacitance	C _{Oes}		-	88	-	
Reverse transfer capacitance	C _{res}		-	12	-	
Gate charge	Q _G	V _{CC} = 520V, I _C = 50.0A, V _{GE} = 15V	-	120.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L _E		-	13.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 50.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 23.1\Omega, R_{G(off)} = 23.1\Omega,$ $L\sigma = 30\text{nH}, C\sigma = 30\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	36	-	ns
Rise time	t_r		-	22	-	ns
Turn-off delay time	$t_{d(off)}$		-	294	-	ns
Fall time	t_f		-	32	-	ns
Turn-on energy	E_{on}		-	0.77	-	mJ
Turn-off energy	E_{off}		-	0.88	-	mJ
Total switching energy	E_{ts}		-	1.65	-	mJ

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Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 25.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 23.1\Omega$, $R_{G(off)} = 23.1\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	33	-	ns
Rise time	t_r		-	14	-	ns
Turn-off delay time	$t_{d(off)}$		-	304	-	ns
Fall time	t_f		-	33	-	ns
Turn-on energy	E_{on}		-	0.36	-	mJ
Turn-off energy	E_{off}		-	0.32	-	mJ
Total switching energy	E_{ts}		-	0.68	-	mJ

Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C}$, $V_R = 400\text{V}$, $I_F = 50.0\text{A}$, $di_F/dt = 2500\text{A}/\mu\text{s}$	-	62	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.40	-	μC
Diode peak reverse recovery current	I_{rrm}		-	40.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1100	-	A/ μs
Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C}$, $V_R = 400\text{V}$, $I_F = 25.0\text{A}$, $di_F/dt = 2500\text{A}/\mu\text{s}$	-	44	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.00	-	μC
Diode peak reverse recovery current	I_{rrm}		-	38.5	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-2200	-	A/ μs

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 150^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 150^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 50.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(\text{on})} = 23.1\Omega$, $R_{G(\text{off})} = 23.1\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	34	-	ns
Rise time	t_r		-	26	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	328	-	ns
Fall time	t_f		-	38	-	ns
Turn-on energy	E_{on}		-	1.00	-	mJ
Turn-off energy	E_{off}		-	1.20	-	mJ
Total switching energy	E_{ts}		-	2.20	-	mJ
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 150^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 25.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(\text{on})} = 23.1\Omega$, $R_{G(\text{off})} = 23.1\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	32	-	ns
Rise time	t_r		-	16	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	354	-	ns
Fall time	t_f		-	44	-	ns
Turn-on energy	E_{on}		-	0.64	-	mJ
Turn-off energy	E_{off}		-	0.56	-	mJ
Total switching energy	E_{ts}		-	1.20	-	mJ

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Diode Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 50.0\text{A},$ $di_F/dt = 2500\text{A}/\mu\text{s}$	-	92	-	ns
Diode reverse recovery charge	Q_{rr}		-	3.20	-	μC
Diode peak reverse recovery current	I_{rrm}		-	63.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1100	-	$\text{A}/\mu\text{s}$
Diode reverse recovery time	t_{rr}	$T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 25.0\text{A},$ $di_F/dt = 2500\text{A}/\mu\text{s}$	-	68	-	ns
Diode reverse recovery charge	Q_{rr}		-	2.30	-	μC
Diode peak reverse recovery current	I_{rrm}		-	59.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1850	-	$\text{A}/\mu\text{s}$

TRENCHSTOP™ 5 soft switching IGBT

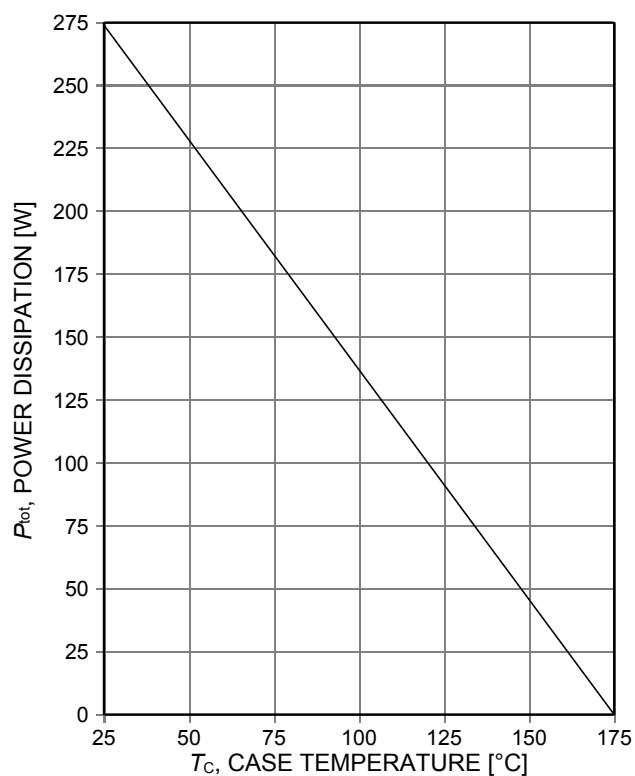


Figure 1. **Power dissipation as a function of case temperature**
($T_{vj} \leq 175^\circ\text{C}$)

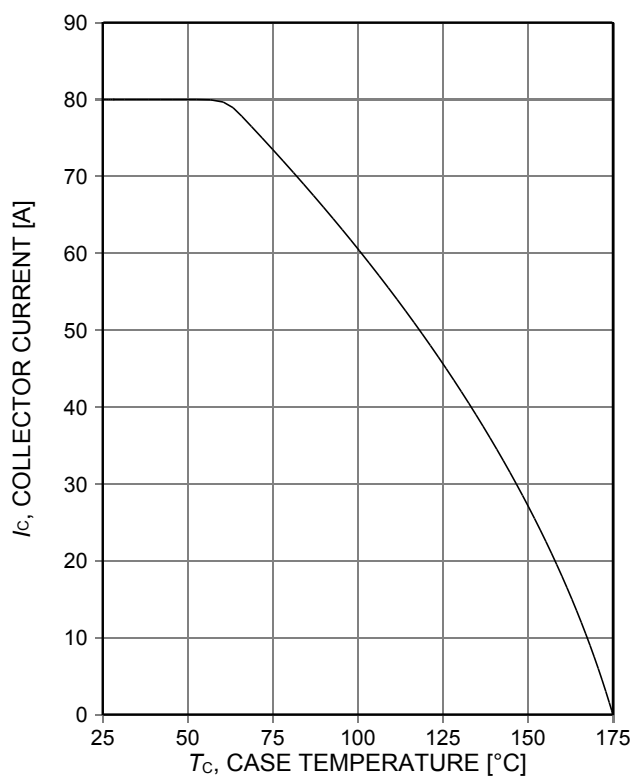


Figure 2. **Collector current as a function of case temperature**
($V_{GE} \geq 15\text{V}$, $T_{vj} \leq 175^\circ\text{C}$)

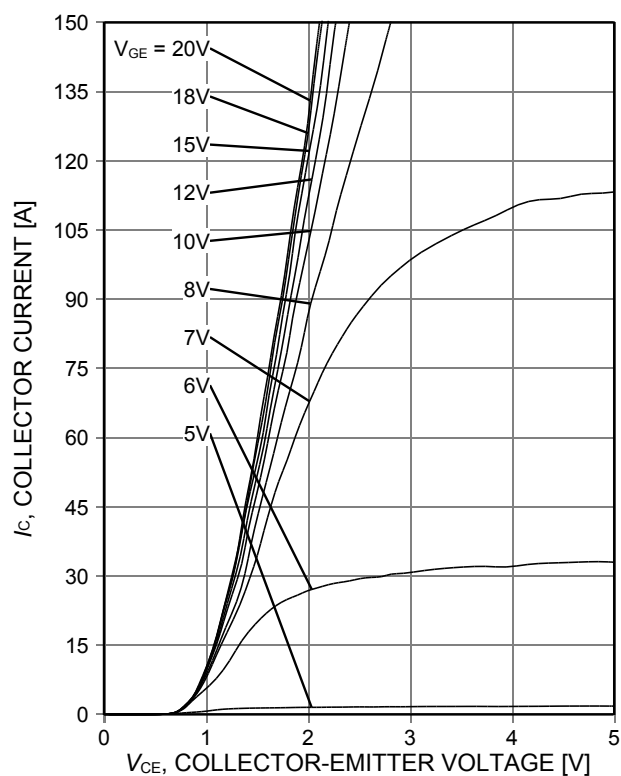


Figure 3. **Typical output characteristic**
($T_{vj} = 25^\circ\text{C}$)

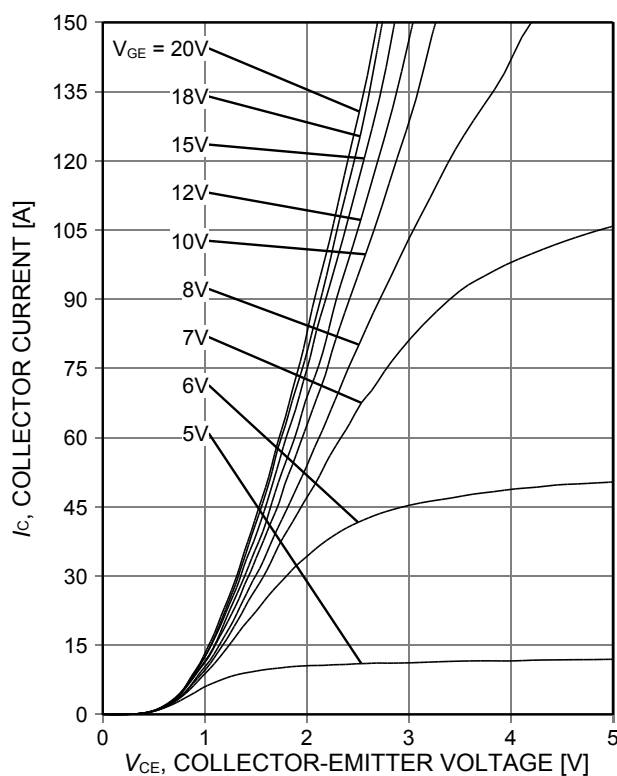


Figure 4. **Typical output characteristic**
($T_{vj} = 175^\circ\text{C}$)

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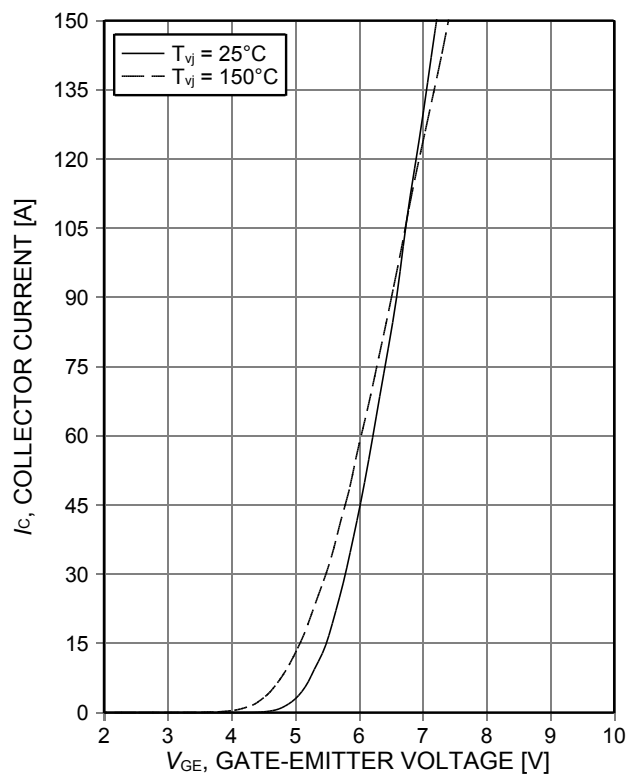


Figure 5. **Typical transfer characteristic**
($V_{CE}=20V$)

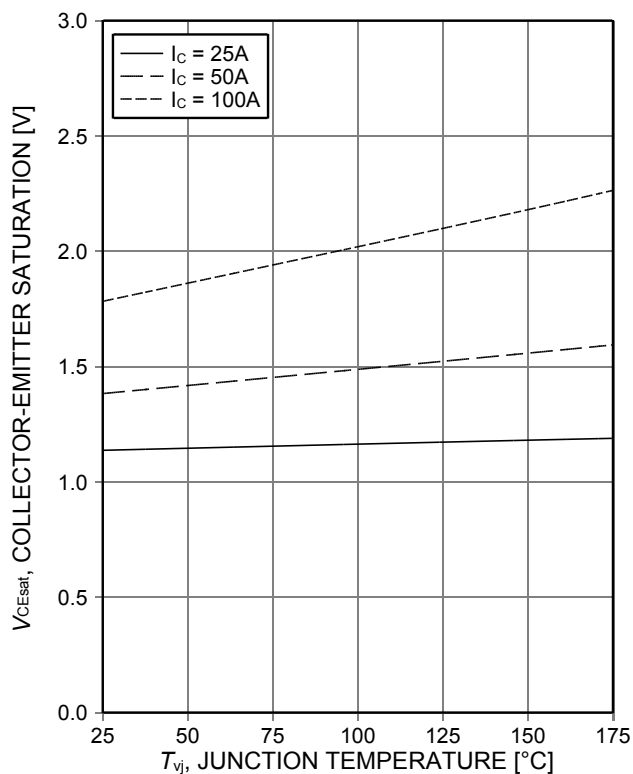


Figure 6. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15V$)

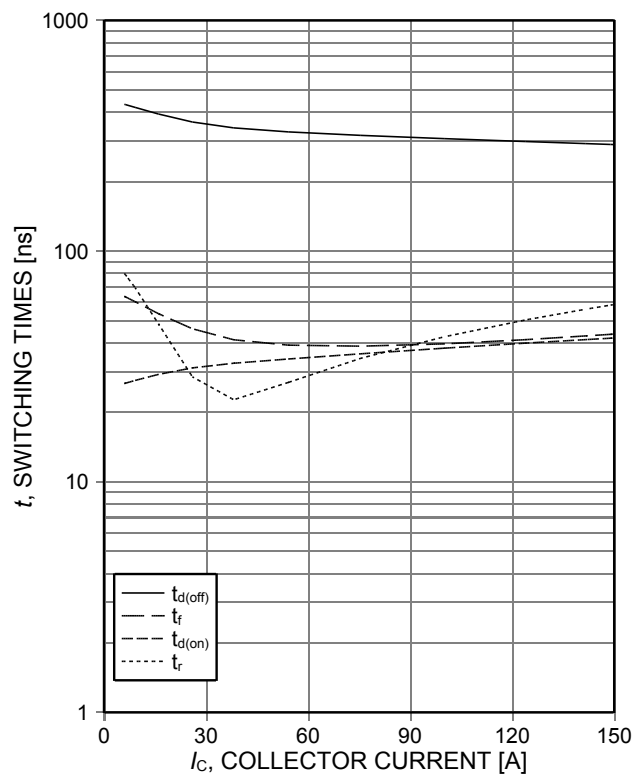


Figure 7. **Typical switching times as a function of collector current**
(inductive load, $T_{vj}=150^{\circ}C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $R_{Gon}=23,1\Omega$, $R_{Goff}=23,1\Omega$, dynamic test circuit in Figure E)

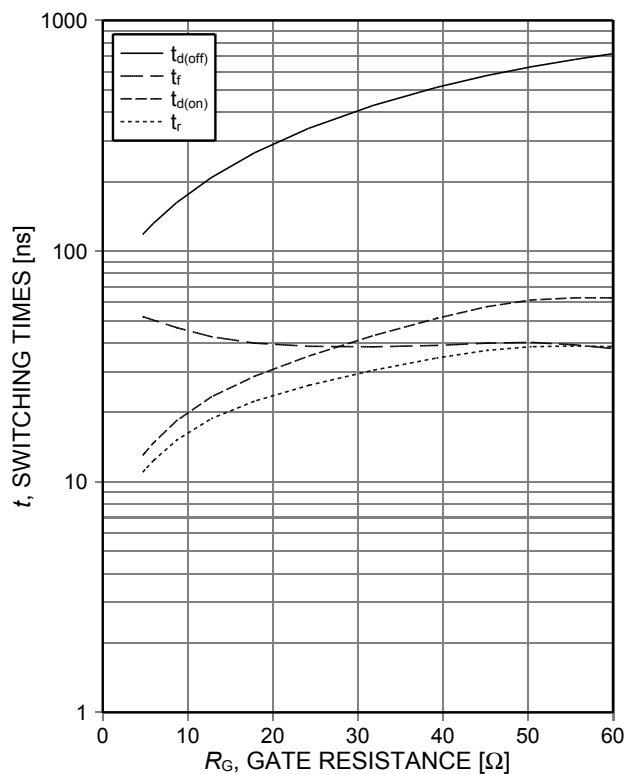


Figure 8. **Typical switching times as a function of gate resistance**
(inductive load, $T_{vj}=150^{\circ}C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=75A$, dynamic test circuit in Figure E)

TRENCHSTOP™ 5 soft switching IGBT

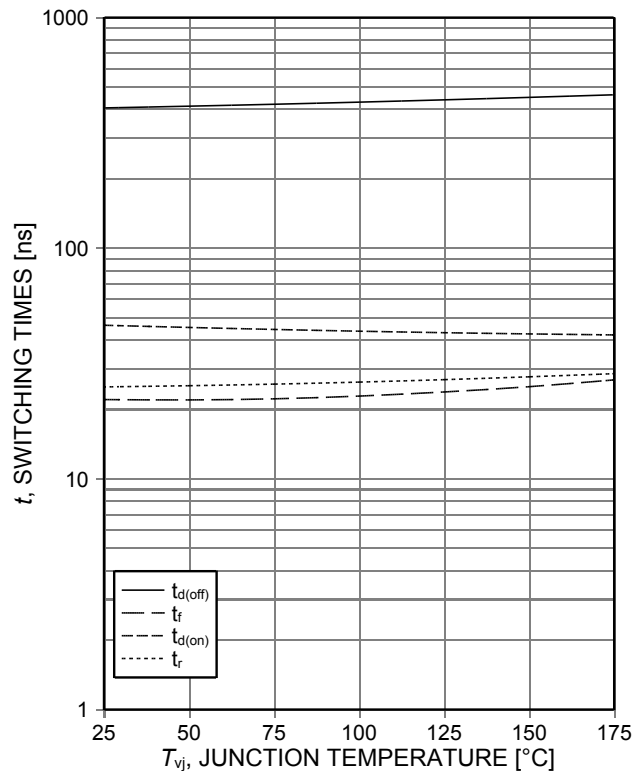


Figure 9. **Typical switching times as a function of junction temperature**
(inductive load, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=75A$, $R_{Gon}=23,1\Omega$, $R_{Goff}=23,1\Omega$, dynamic test circuit in Figure E)

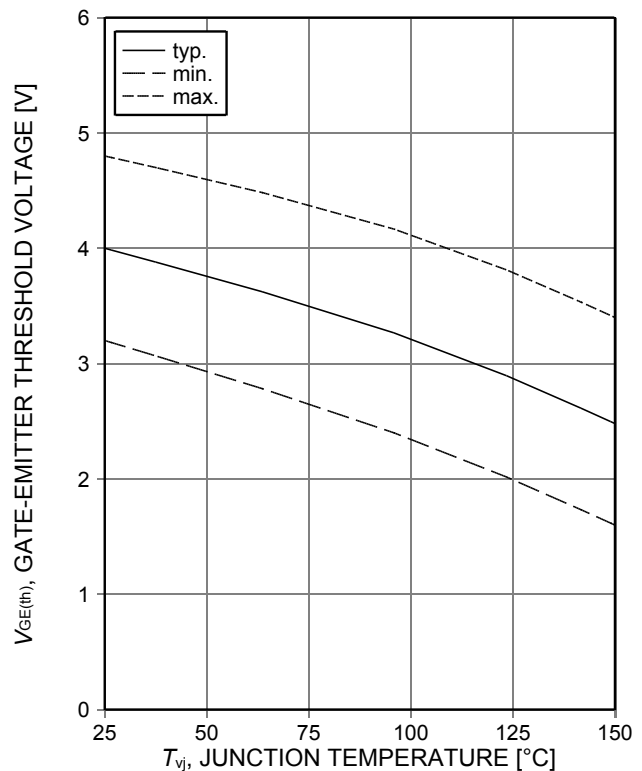


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**
($I_C=0.5mA$)

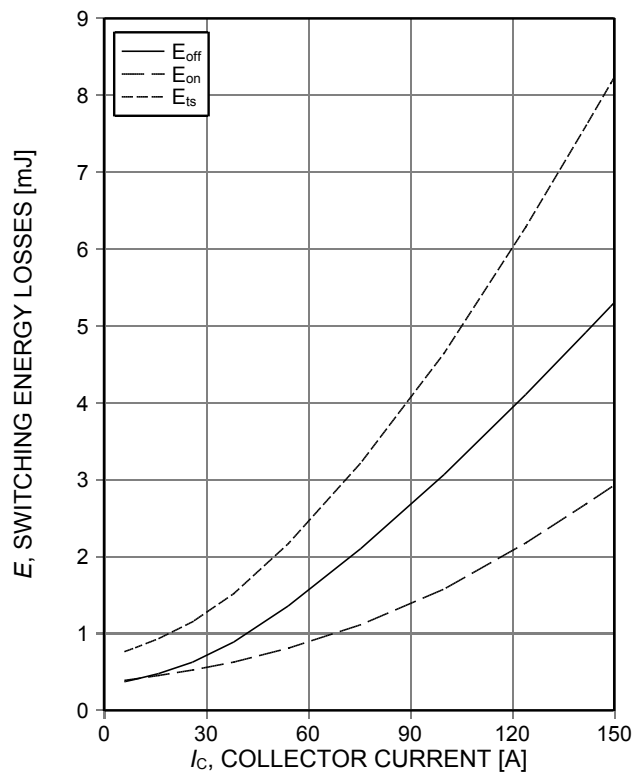


Figure 11. **Typical switching energy losses as a function of collector current**
(inductive load, $T_{vj}=150^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $R_{Gon}=23,1\Omega$, $R_{Goff}=23,1\Omega$, dynamic test circuit in Figure E)

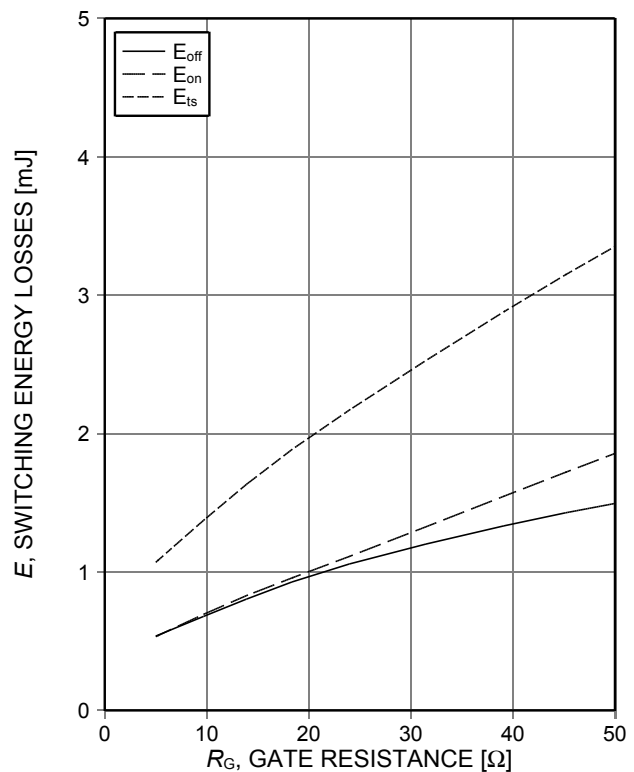


Figure 12. **Typical switching energy losses as a function of gate resistance**
(inductive load, $T_{vj}=150^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=75A$, dynamic test circuit in Figure E)

TRENCHSTOP™ 5 soft switching IGBT

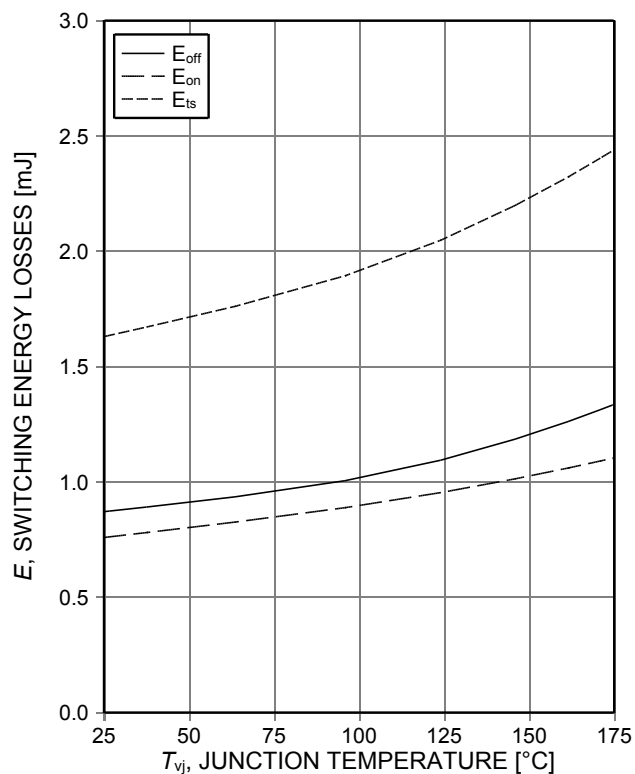


Figure 13. **Typical switching energy losses as a function of junction temperature**
(inductive load, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=75A$, $R_{Gon}=23,1\Omega$, $R_{Goff}=23,1\Omega$, dynamic test circuit in Figure E)

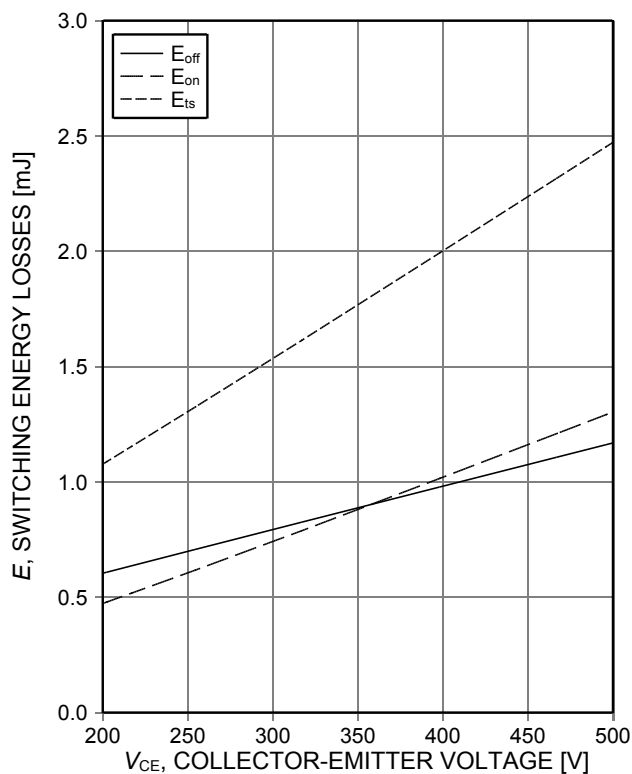


Figure 14. **Typical switching energy losses as a function of collector emitter voltage**
(inductive load, $T_{vj}=150^\circ C$, $V_{GE}=0/15V$, $I_C=75A$, $R_{Gon}=23,1\Omega$, $R_{Goff}=23,1\Omega$, dynamic test circuit in Figure E)

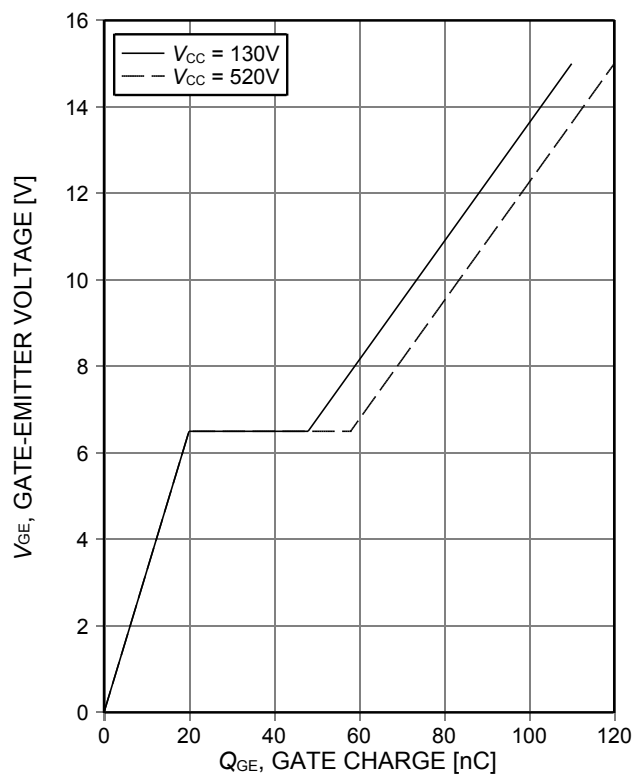


Figure 15. **Typical gate charge**
($I_C=75A$)

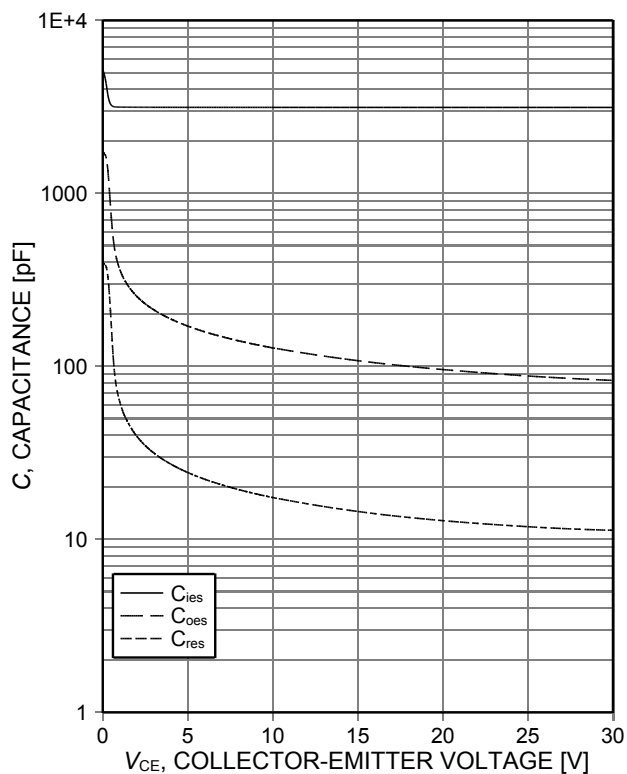


Figure 16. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0V$, $f=1MHz$)

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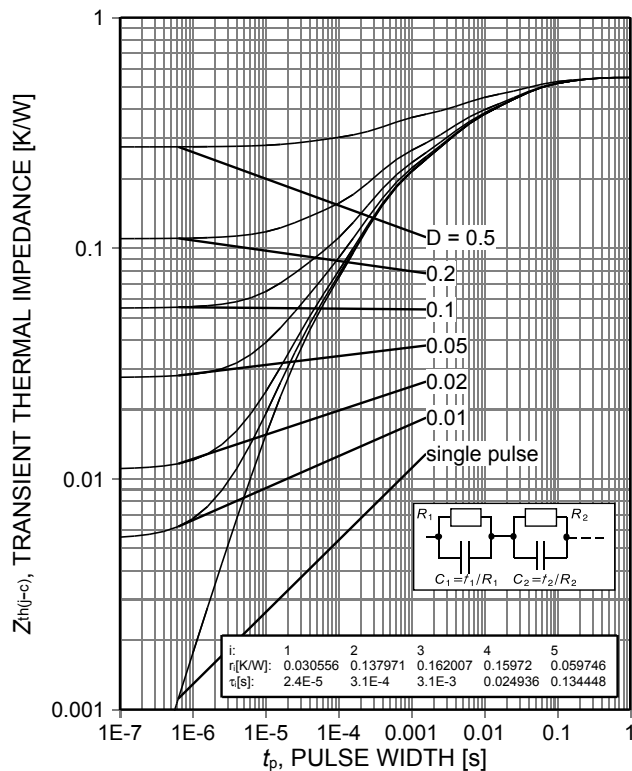


Figure 17. IGBT transient thermal impedance ($D=t_p/T$)

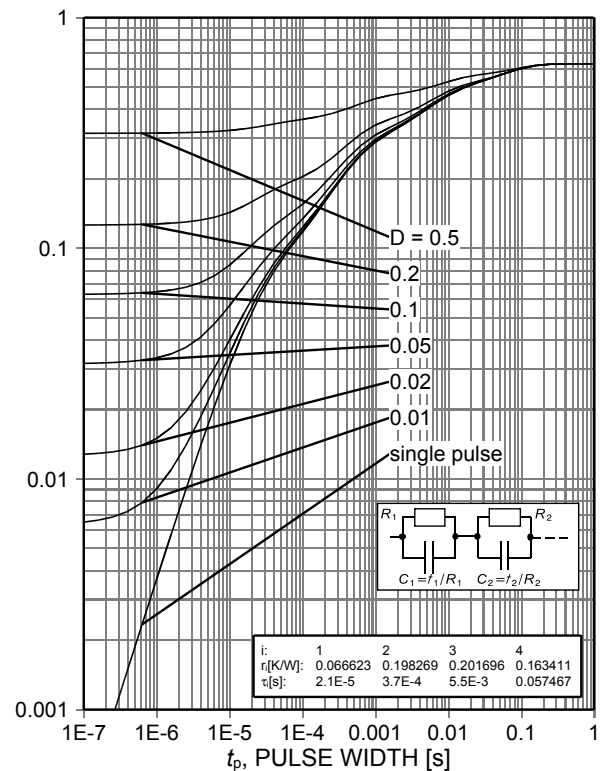


Figure 18. Diode transient thermal impedance as a function of pulse width ($D=t_p/T$)

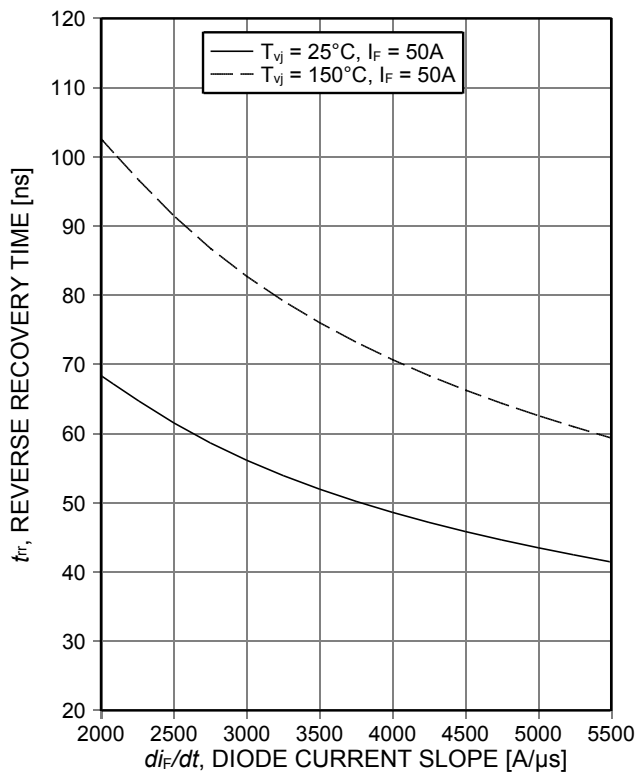


Figure 19. Typical reverse recovery time as a function of diode current slope ($V_R=400V$)

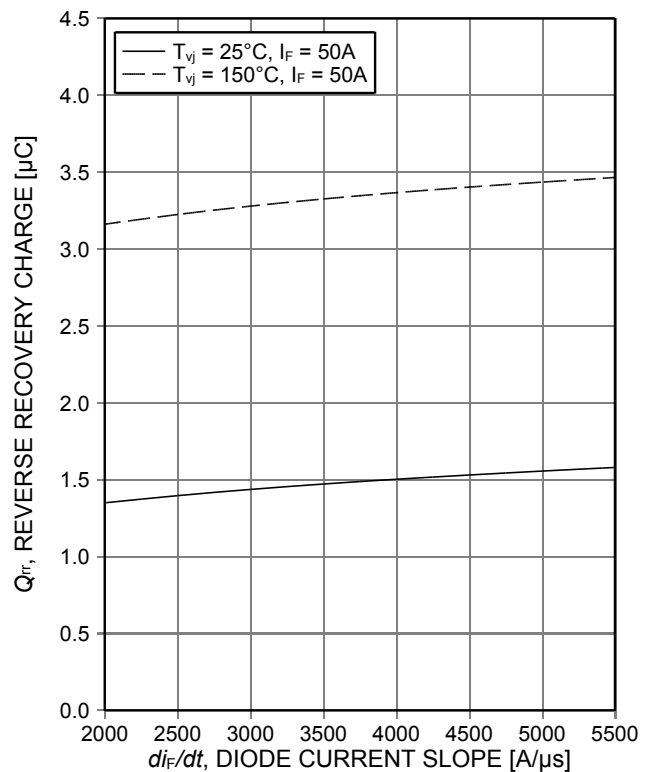


Figure 20. Typical reverse recovery charge as a function of diode current slope ($V_R=400V$)

TRENCHSTOP™ 5 soft switching IGBT

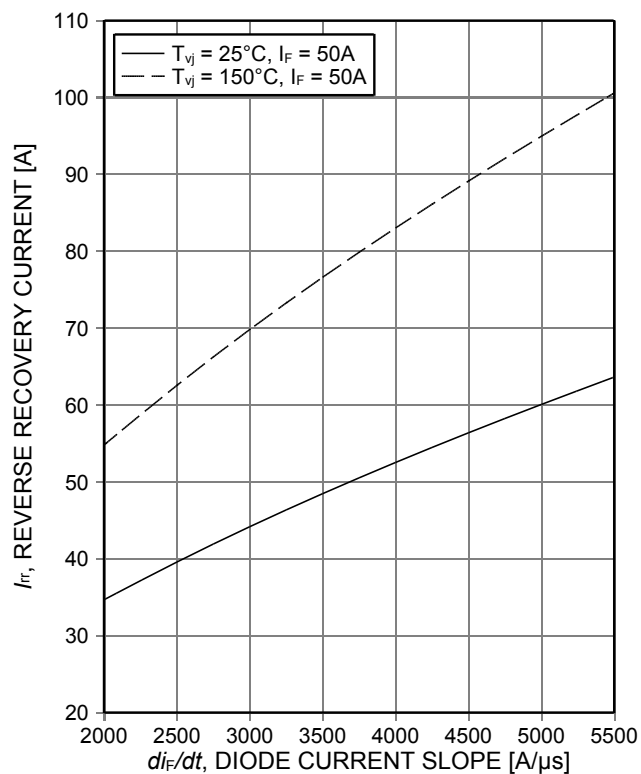


Figure 21. Typical reverse recovery current as a function of diode current slope ($V_R=400V$)

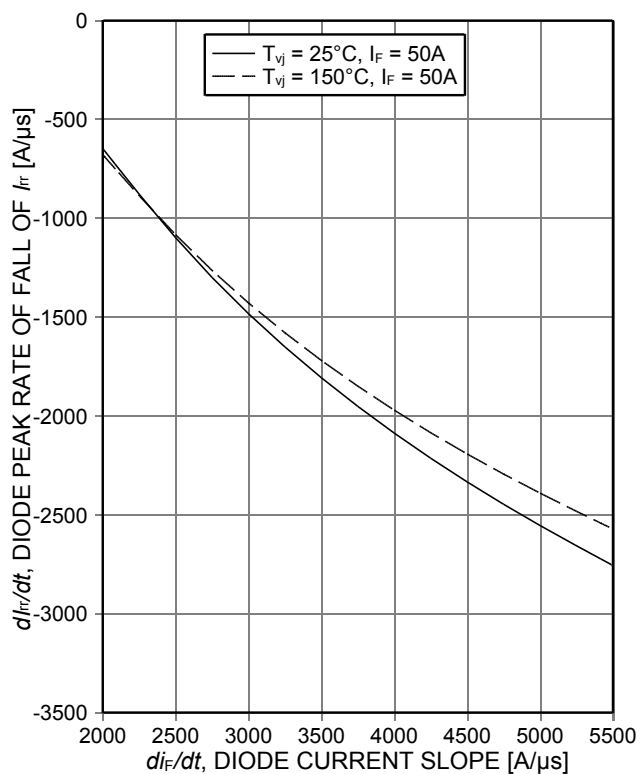


Figure 22. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ($V_R=400V$)

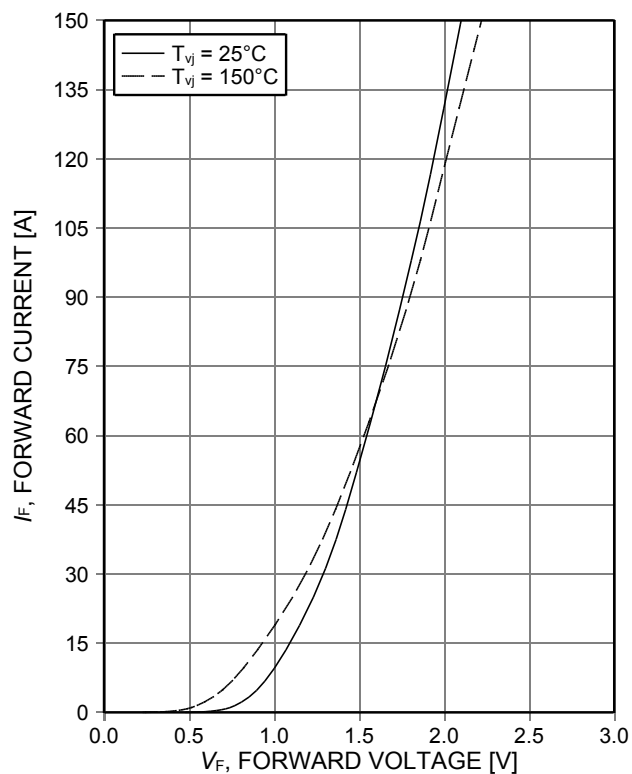


Figure 23. Typical diode forward current as a function of forward voltage

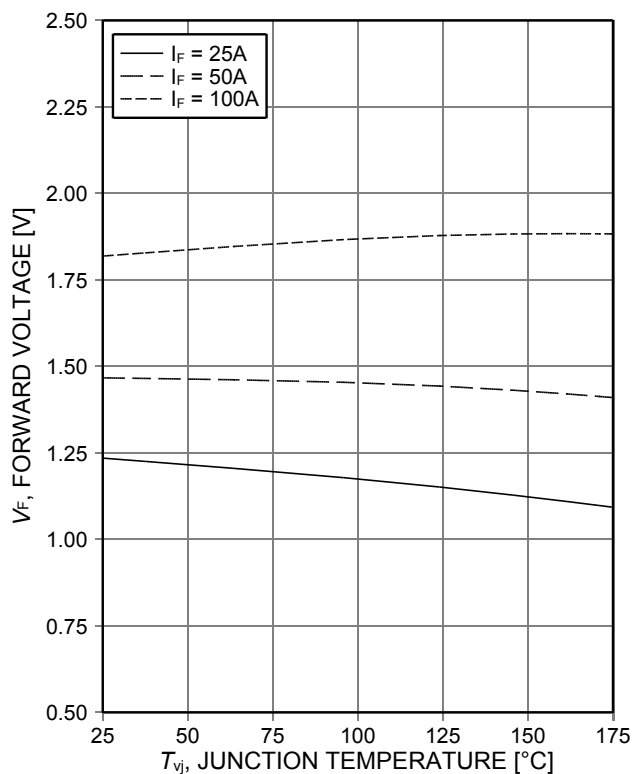
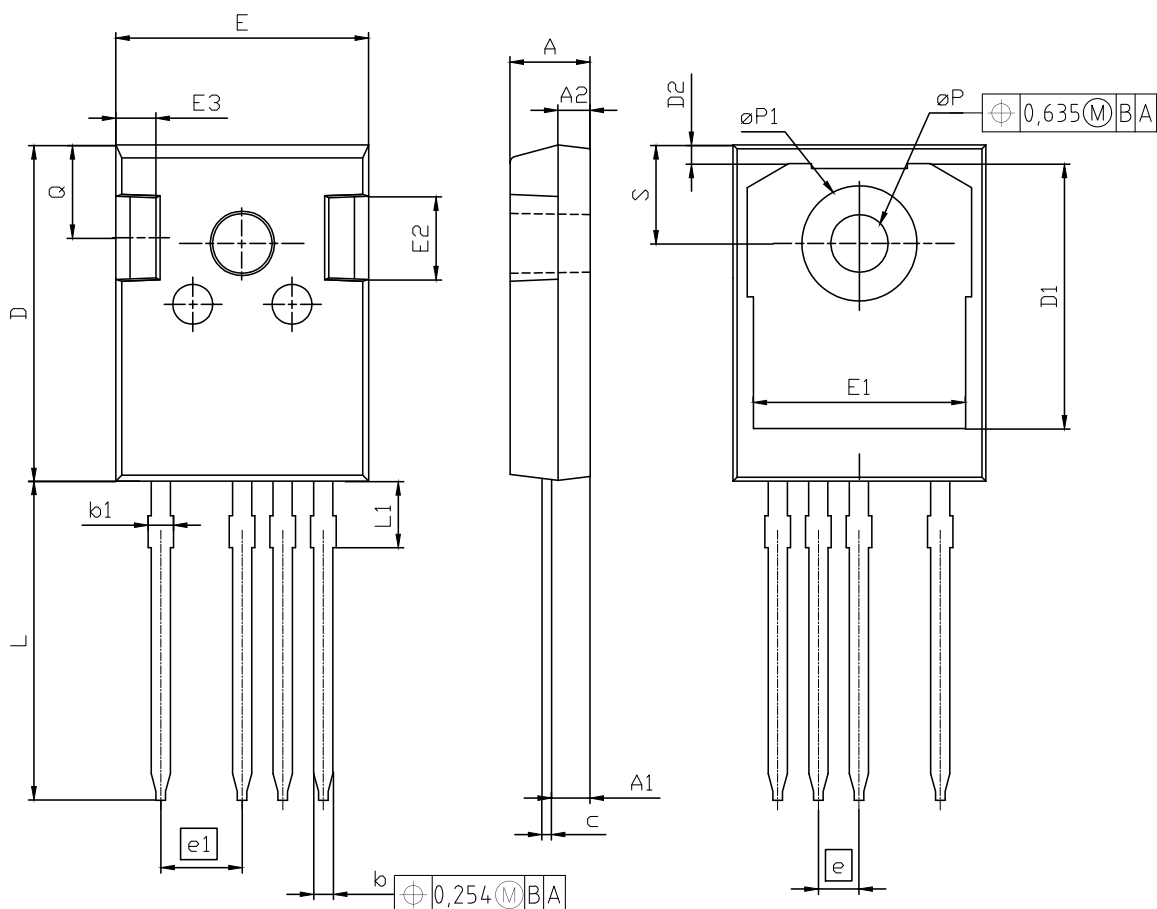


Figure 24. Typical diode forward voltage as a function of junction temperature

TRENCHSTOP™ 5 soft switching IGBT

Package Drawing PG-TO247-4



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.90	2.16	0.075	0.085
b	1.07	1.33	0.042	0.052
b1	1.10	1.70	0.043	0.067
c	0.50	0.70	0.020	0.028
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	2.54 (BSC)		0.100 (BSC)	
e1	5.08		0.200	
N	4		4	
L	19.72	20.32	0.776	0.800
L1	4.02	4.40	0.158	0.173
øP	3.50	3.70	0.138	0.146
øP1	7.00	7.40	0.276	0.291
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO. Z8B00168124
SCALE
EUROPEAN PROJECTION
ISSUE DATE 29-01-2013
REVISION 1

Testing Conditions



Figure A. Definition of switching times



Figure B. Definition of switching losses

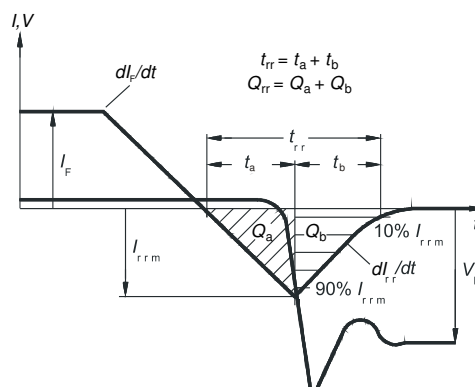


Figure C. Definition of diode switching characteristics

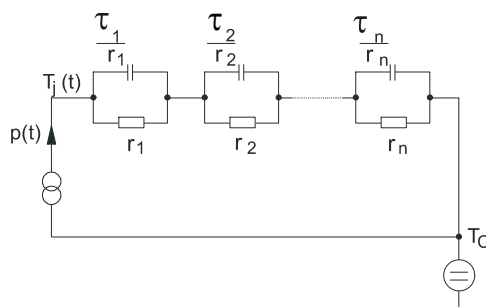


Figure D. Thermal equivalent circuit

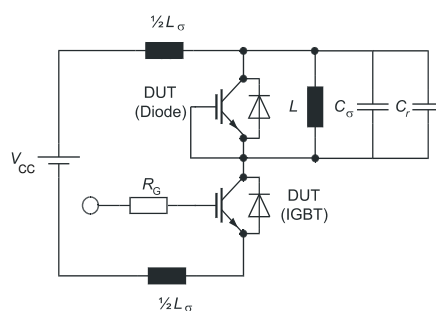


Figure E. **Dynamic test circuit**
Parasitic inductance L_σ ,
parasitic capacitor C_σ ,
relief capacitor C_r ,
(only for ZVT switching)

TRENCHSTOP™ 5 soft switching IGBT

Revision History

IKZ50N65ES5

Revision: 2017-04-26, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2017-04-26	Final data sheet

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